MDD175-34N1

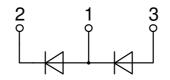
High Voltage Standard Rectifier Module		= 2x 3400 \	
	I _{FAV}	=	240 A
	V_{F}	=	1.01 V

Phase leg

Part number MDD175-34N1



Backside: isolated **E**72873



Features / Advantages:

- Planar passivated chips
- Very low leakage current
- Very low forward voltage drop
- Improved thermal behaviour

Applications:

- Diode for main rectification
- For single and three phase
- bridge configurations
- Supplies for DC power equipment
- Input rectifiers for PWM inverter
- Battery DC power supplies
- · Field supply for DC motors

Package: Y1

- Isolation Voltage: 4800 V~
- Industry standard outline
- RoHS compliant
- Base plate: Copper
- internally DCB isolated
- Advanced power cycling

Terms Conditions of usage:

The data contained in this product data sheet is exclusively intended for technically trained staff. The user will have to evaluate the suitability of the product for the intended application and the completeness of the product data with respect to his application. The specifications of our components may not be considered as an assurance of component characteristics. The information in the valid application and assembly notes must be considered. Should you require product information in excess of the data given in this product data sheet or which concerns the specific application of your product, please contact your local sales office. Due to technical requirements our product may contain dangerous substances. For information on the types in question please contact your local sales office. Should you intend to use the product in aviation, in health or life endangering or life support applications, please notify. For any such application we urgently recommend

to perform joint risk and quality assessments;
the conclusion of quality agreements;

- to establish joint measures of an ongoing product survey, and that we may make delivery dependent on the realization of any such measures.

IXYS reserves the right to change limits, conditions and dimensions.

Data according to IEC 60747and per semiconductor unless otherwise specified

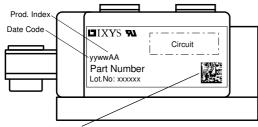
MDD175-34N1

Rectifier			Ratings				
Symbol	Definition	Conditions		min.	typ.	max.	Unit
V _{RSM}	max. non-repetitive reverse bloc	king voltage	$T_{VJ} = 25^{\circ}C$			3500	V
V _{RRM}	max. repetitive reverse blocking	voltage	$T_{VJ} = 25^{\circ}C$			3400	V
I _R	reverse current	$V_{R} = 3400 V$	$T_{VJ} = 25^{\circ}C$			1	mA
		$V_{R} = 3400 V$	$T_{vJ} = 150^{\circ}C$			5	mA
V _F	forward voltage drop	I _F = 200 A	$T_{VJ} = 25^{\circ}C$			1.07	V
		I _F = 400 A				1.26	V
		$I_{F} = 200 \text{ A}$	T _{vJ} = 125 °C			1.01	V
		$I_{F} = 400 \text{ A}$				1.26	V
FAV	average forward current	T _c = 100°C	T _{vJ} = 150°C			240	Α
		180° sine d = 0.5					
V _{F0}	threshold voltage		T _{vj} = 150°C			0.74	V
r _F	slope resistance } for power	loss calculation only				1.27	mΩ
R _{thJC}	thermal resistance junction to ca	ase				0.14	K/W
R _{thCH}	thermal resistance case to heats	sink			0.04		K/W
P _{tot}	total power dissipation		$T_c = 25^{\circ}C$			900	W
I _{FSM}	max. forward surge current	t = 10 ms; (50 Hz), sine	$T_{VJ} = 45^{\circ}C$			8.50	kA
		t = 8,3 ms; (60 Hz), sine	$V_{R} = 0 V$			9.18	kA
		t = 10 ms; (50 Hz), sine	T _{vJ} = 150°C			7.23	kA
		t = 8,3 ms; (60 Hz), sine	$V_{R} = 0 V$			7.81	kA
l²t	value for fusing	t = 10 ms; (50 Hz), sine	$T_{VJ} = 45^{\circ}C$			361.3	kA²s
		t = 8,3 ms; (60 Hz), sine	$V_{R} = 0 V$			350.6	kA²s
		t = 10 ms; (50 Hz), sine	$T_{vJ} = 150^{\circ}C$			261.0	kA²s
		t = 8,3 ms; (60 Hz), sine	$V_{R} = 0 V$			253.4	kA²s
C	junction capacitance	V _B = 1100 V; f = 1 MHz	$T_{vJ} = 25^{\circ}C$		182		pF

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MDD175-34N1

Package Y1				Ratings			
Symbol	Definition	Conditions		min.	typ.	max.	Unit
I _{RMS}	RMS current	per terminal				600	Α
T _{vj}	virtual junction temperature		-40		150	°C	
T _{op}	operation temperature		-40		125	°C	
T _{stg}	storage temperature		-40		125	°C	
Weight					680		g
M _D	mounting torque			4.5		7	Nm
M _T	terminal torque			11		13	Nm
d _{Spp/App}	creepage distance on surface striking distance through a		terminal to terminal	16.0			mm
d _{Spb/Apb}			terminal to backside	16.0			mm
	isolation voltage t = 1 second t = 1 minute	t = 1 second		4800			V
		t = 1 minute	50/60 Hz, RMS; liso∟ ≤ 1 mA	4000			V



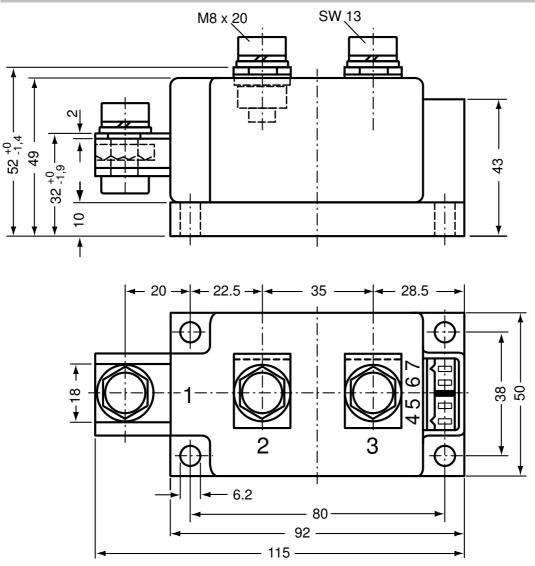
Data Matrix: *Typ* (1-19), DC+*Prod.Index* (20-25), *FKT#* (26-31) *leer* (33), *lfd.#* (33-36)

ſ	Ordering	Ordering Number	Marking on Product	Delivery Mode	Quantity	Code No.
	Standard	MDD175-34N1	MDD175-34N1	Box	3	504075

Equiva	alent Circuits for	Simulation	* on die level	T _{vj} = 150 °C
)[Rectifier		
V _{0 max}	threshold voltage	0.74		V
$\mathbf{R}_{0 \text{ max}}$	slope resistance *	0.75		mΩ

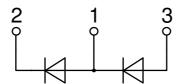
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Outlines Y1



Optional accessories for modules

Keyed gate/cathode twin plugs with wire length = 350 mm, gate = white, cathode = red Type ZY 180L (L = Left for pin pair 4/5) Type ZY 180R (R = Right for pin pair 6/7) UL 758, style 3751



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Rectifier

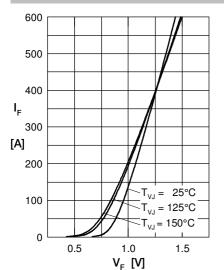
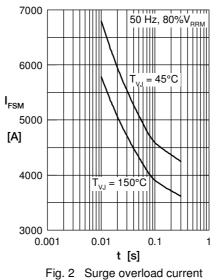
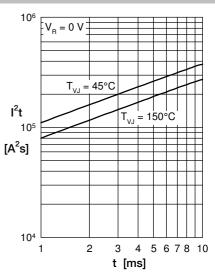


Fig. 1 Forward current versus

voltage drop per diode







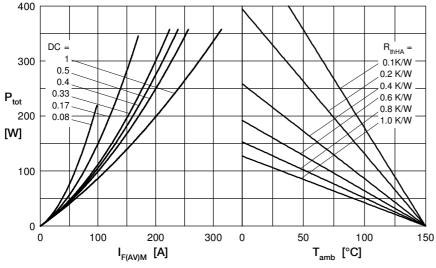
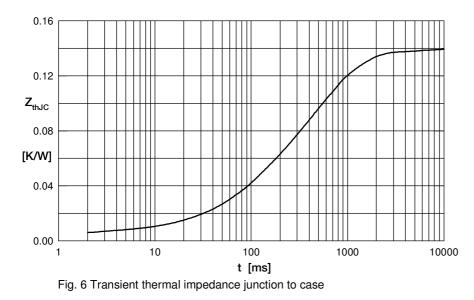


Fig. 4 Power dissipation vs. direct output current and ambient temperature



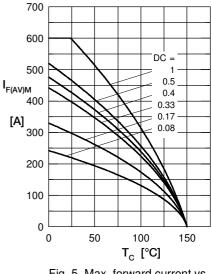


Fig. 5 Max. forward current vs. case temperature

Constants for Z_{thJC} calculation:

i	R _{thi} (K/W)	t _i (s)
1	0.155	0.0005
2	0.332	0.0095
3	0.713	0.17
4	0.3	0.8
5	0.00001	0.00001

